

# Benjamin Iñiguez

## List of Publications by Year in descending order

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docs citations

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times ranked

2232  
citing authors

#	ARTICLE	IF	CITATIONS
1	Physics-Based DC Compact Modeling of Schottky Barrier and Reconfigurable Field-Effect Transistors. IEEE Journal of the Electron Devices Society, 2022, 10, 416-423.	2.1	7
2	Quasi-Compact Model of Direct Source-to-Drain Tunneling Current in Ultrashort-Channel Nanosheet MOSFETs by Wavelet Transform. IEEE Transactions on Electron Devices, 2022, 69, 17-24.	3.0	4
3	Modeling the Short-Channel Effects in Coplanar Organic Thin-Film Transistors. IEEE Transactions on Electron Devices, 2022, 69, 1099-1106.	3.0	2
4	Cryogenic Temperature and Doping Analysis of Source-to-Drain Tunneling Current in Ultrashort-Channel Nanosheet MOSFETs. IEEE Transactions on Electron Devices, 2022, 69, 1588-1595.	3.0	4
5	Foreword Special Issue on the 3rd Latin American Electron Device Conference. IEEE Journal of the Electron Devices Society, 2022, 10, 413-415.	2.1	0
6	Noise-Based Simulation Technique for Circuit-Variability Analysis. IEEE Journal of the Electron Devices Society, 2021, 9, 450-455.	2.1	3
7	New Compact Modeling Solutions for Organic and Amorphous Oxide TFTs. IEEE Journal of the Electron Devices Society, 2021, 9, 911-932.	2.1	8
8	Foreword Special Issue on the 2nd Latin American Electron Device Conference. IEEE Journal of the Electron Devices Society, 2021, 9, 447-449.	2.1	0
9	Compact DC and Quasi-Static Capacitances Modeling of a-Si:H TFTs, Including Parasitic Capacitances. IEEE Transactions on Electron Devices, 2021, 68, 3384-3389.	3.0	4
10	Compact Modeling of Nonlinear Contact Effects in Short-Channel Coplanar and Staggered Organic Thin-Film Transistors. IEEE Transactions on Electron Devices, 2021, 68, 3843-3850.	3.0	15
11	Flexible megahertz organic transistors and the critical role of the device geometry on their dynamic performance. Journal of Applied Physics, 2021, 130, .	2.5	6
12	Dynamic Simulation of a-IGZO TFT Circuits Using the Analytical Full Capacitance Model (AFCM). IEEE Journal of the Electron Devices Society, 2021, 9, 464-468.	2.1	1
13	Non-Linear Output-Conductance Function for Robust Analysis of Two-Dimensional Transistors. IEEE Electron Device Letters, 2021, 42, 94-97.	3.9	2
14	Charge-Based Model for the Drain-Current Variability in Organic Thin-Film Transistors Due to Carrier-Number and Correlated- Mobility Fluctuation. IEEE Transactions on Electron Devices, 2020, 67, 4667-4671.	3.0	8
15	Macromodel for AC and Transient Simulations of Organic Thin-Film Transistor Circuits Including Nonquasistatic Effects. IEEE Transactions on Electron Devices, 2020, 67, 4672-4676.	3.0	4
16	Advances in Compact Modeling of Organic Field-Effect Transistors. IEEE Journal of the Electron Devices Society, 2020, 8, 1404-1415.	2.1	23
17	Compact Modeling of Short-Channel Effects in Staggered Organic Thin-Film Transistors. IEEE Transactions on Electron Devices, 2020, 67, 5082-5090.	3.0	7
18	Foreword Special Issue on Compact Modeling of Semiconductor Devices. IEEE Journal of the Electron Devices Society, 2020, 8, 1350-1353.	2.1	0

#	ARTICLE	IF	CITATIONS
19	Equivalent DG Dimensions Concept for Compact Modeling of Short-Channel and Thin Body GAA MOSFETs Including Quantum Confinement. IEEE Transactions on Electron Devices, 2020, 67, 5381-5387.	3.0	4
20	Direct Source-to-Drain Tunneling Current in Ultra-Short Channel DG MOSFETs by Wavelet Transform. , 2020, , .		3
21	Charge-Based Compact Modeling of Capacitances in Staggered Multi-Finger OTFTs. IEEE Journal of the Electron Devices Society, 2020, 8, 396-406.	2.1	10
22	Parameter Extraction and Compact Modeling of 1/f Noise for Amorphous ESL IGZO TFTs. IEEE Journal of the Electron Devices Society, 2020, 8, 407-412.	2.1	6
23	Analytical Current-Voltage Model for Double-Gate a-IGZO TFTs With Symmetric Structure for Above Threshold. IEEE Transactions on Electron Devices, 2020, 67, 1980-1986.	3.0	5
24	Parameter Extraction and Compact Modeling of OTFTs From 150 K to 350 K. IEEE Transactions on Electron Devices, 2020, 67, 5685-5692.	3.0	5
25	Analytical Model for Threshold-Voltage Shift in Submicron Staggered Organic Thin-Film Transistors. , 2019, , .		1
26	1/f noise analysis in high mobility polymer-based OTFTs with non-fluorinated dielectric. Applied Physics Letters, 2019, 114, .	3.3	7
27	A Piecewise Approximation for Short-Channel "Extrinsic" MOSFET Drain Current Dependence on Drain-to-Source Bias Including Linear Triode, Linear Saturation and Asymptotic Saturation Regimes. ECS Transactions, 2019, 90, 101-112.	0.5	1
28	Analysis and Compact Modeling of Gate Capacitance in Organic Thin-Film Transistors. IEEE Transactions on Electron Devices, 2019, 66, 2370-2374.	3.0	8
29	A Complete Charge-Based Capacitance Model for IGZO TFTs. IEEE Electron Device Letters, 2019, 40, 730-733.	3.9	10
30	Full capacitance model, considering the specifics of amorphous oxide semiconductor thin film transistors structures. Solid-State Electronics, 2019, 156, 16-22.	1.4	7
31	Analytical modeling of capacitances in tunnel-FETs including the effect of Schottky barrier contacts. Solid-State Electronics, 2019, 159, 191-196.	1.4	6
32	Current-voltage and flicker noise analysis and unified modeling for amorphous indium-gallium-zinc-oxide thin film transistors with etch stop layer from 298 to 333 K. Journal of Applied Physics, 2019, 125, .	2.5	6
33	Equivalent Length Concept for Compact Modeling of Short-Channel GAA and DG MOSFETs. , 2019, , .		2
34	Features of the Nonlinear Harmonic Distortion in AOSTFTs. IEEE Transactions on Electron Devices, 2019, 66, 5177-5182.	3.0	1
35	An analytical drain current model for cylindrical gate DMG-GC-DOT MOSFET. International Journal of Electronics Letters, 2019, 7, 458-472.	1.2	3
36	Advanced analytical modeling of double-gate Tunnel-FETs - A performance evaluation. Solid-State Electronics, 2018, 141, 31-39.	1.4	9

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37	Analytical Model for Schottky Barrier Height and Threshold Voltage of AlGaIn/GaN HEMTs With Piezoelectric Effect. IEEE Transactions on Electron Devices, 2018, 65, 901-907.	3.0	21
38	Compact mole fraction-dependent modeling of I-V and C-V characteristics in Al <sub>x</sub> Ga <sub>1-x</sub> N/GaN HEMTs. Journal of Computational Electronics, 2018, 17, 224-229.	2.5	2
39	Compact Modelling of Quantum Confinement in III-V Gate All Around Nanowire MOSFET. , 2018, , .		3
40	Compact modelling for quantum confinement for InGaAs nanowire gate all around MOSFET. Electronics Letters, 2018, 54, 1348-1350.	1.0	2
41	Accurate semi empirical predictive model for doped and undoped double gate MOSFET. Solid-State Electronics, 2018, 149, 23-31.	1.4	1
42	An insight to mobility parameters for AOSTFTs, when the effect of both, localized and free carriers, must be considered to describe the device behavior. Solid-State Electronics, 2018, 149, 32-37.	1.4	10
43	A compact explicit DC model for short channel Gate-All-Around junctionless MOSFETs. Solid-State Electronics, 2017, 131, 24-29.	1.4	12
44	Charge based, continuous compact model for the channel current in organic thin-film transistors for all regions of operation. Solid-State Electronics, 2017, 133, 17-24.	1.4	22
45	Analytical high frequency GaN HEMT model for noise simulations. Semiconductor Science and Technology, 2017, 32, 125012.	2.0	2
46	A quantum wave based compact modeling approach for the current in ultra-short DG MOSFETs suitable for rapid multi-scale simulations. Solid-State Electronics, 2017, 137, 70-79.	1.4	0
47	Crystalline-like temperature dependence of the electrical characteristics in amorphous Indium-Gallium-Zinc-Oxide thin film transistors. Solid-State Electronics, 2017, 135, 43-48.	1.4	7
48	On the series resistance in staggered amorphous thin film transistors. Microelectronics Reliability, 2016, 63, 325-335.	1.7	14
49	A compact model and direct parameters extraction techniques For amorphous gallium-indium-zinc-oxide thin film transistors. Solid-State Electronics, 2016, 126, 81-86.	1.4	24
50	DC self-heating effects modelling in SOI and bulk FinFETs. Microelectronics Journal, 2015, 46, 320-326.	2.0	20
51	Compact model for short-channel symmetric double-gate junctionless transistors. Solid-State Electronics, 2015, 111, 196-203.	1.4	18
52	An analytical 3D model for short-channel effects in undoped FinFETs. Journal of Computational Electronics, 2015, 14, 500-505.	2.5	5
53	A complete and Verilog-A compatible Gate-All-Around long-channel junctionless MOSFET model implemented in CMOS inverters. Microelectronics Journal, 2015, 46, 1069-1072.	2.0	2
54	3-D compact model for nanoscale junctionless triple-gate nanowire MOSFETs, including simple treatment of quantization effects. Solid-State Electronics, 2015, 112, 85-98.	1.4	18

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55	Experimentally verified drain-current model for variable barrier transistor. Electronics Letters, 2015, 51, 1364-1366.	1.0	4
56	Graphene electronic sensors – review of recent developments and future challenges. IET Circuits, Devices and Systems, 2015, 9, 446-453.	1.4	51
57	Modeling of temperature effects in a surface-potential based ASM-HEMT model. , 2014, , .		10
58	Foreword Special Issue on Compact Modeling of Emerging Devices. IEEE Transactions on Electron Devices, 2014, 61, 221-224.	3.0	0
59	Modeling and performance study of nanoscale double gate junctionless and inversion mode MOSFETs including carrier quantization effects. Microelectronics Journal, 2014, 45, 1220-1225.	2.0	9
60	Pseudo-Boltzmann model for modeling the junctionless transistors. Solid-State Electronics, 2014, 95, 19-22.	1.4	7
61	Compact core model for Symmetric Double-Gate Junctionless Transistors. Solid-State Electronics, 2014, 94, 91-97.	1.4	21
62	A Compact Explicit Model for Long-Channel Gate-All-Around Junctionless MOSFETs. Part I: DC Characteristics. IEEE Transactions on Electron Devices, 2014, 61, 3036-3041.	3.0	36
63	Compact Capacitance Model for OTFTs at Low and Medium Frequencies. IEEE Transactions on Electron Devices, 2014, 61, 638-642.	3.0	13
64	A Compact Explicit Model for Long-Channel Gate-All-Around Junctionless MOSFETs. Part II: Total Charges and Intrinsic Capacitance Characteristics. IEEE Transactions on Electron Devices, 2014, 61, 3042-3046.	3.0	22
65	Analytical temperature dependent model for nanoscale double-gate MOSFETs reproducing advanced transport models. Solid-State Electronics, 2014, 98, 2-6.	1.4	4
66	A 2D closed form model for the electrostatics in hetero-junction double-gate tunnel-FETs for calculation of band-to-band tunneling current. Microelectronics Journal, 2014, 45, 1144-1153.	2.0	26
67	Characterization of MIS structures and PTFTs using TiOx deposited by spin-coating. Microelectronics Reliability, 2014, 54, 893-898.	1.7	1
68	Charge-based continuous model for long-channel Symmetric Double-Gate Junctionless Transistors. Solid-State Electronics, 2013, 85, 59-63.	1.4	37
69	A compact charge-based physical model for AlGaIn/GaN HEMTs. , 2013, , .		4
70	A Compact Model for Organic Field-Effect Transistors With Improved Output Asymptotic Behaviors. IEEE Transactions on Electron Devices, 2013, 60, 1136-1141.	3.0	85
71	Implementation of nanoscale double-gate CMOS circuits using compact advanced transport models. Microelectronics Journal, 2013, 44, 80-85.	2.0	6
72	Compact drain-current model for undoped cylindrical surrounding-gate metal-oxide-semiconductor field effect transistors including short channel effects. Journal of Applied Physics, 2013, 114, .	2.5	17

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73	Threshold voltage, and 2D potential modeling within short-channel junctionless DG MOSFETs in subthreshold region. Solid-State Electronics, 2013, 90, 107-115.	1.4	52
74	A compact charge-based physical model for AlGaIn/GaN HEMTs. , 2013, , .		1
75	A compact charge-based physical model for AlGaIn/GaN HEMTs. , 2013, , .		2
76	A simple compact model for long-channel junctionless Double Gate MOSFETs. Solid-State Electronics, 2013, 80, 28-32.	1.4	34
77	Modeling of low frequency noise in FD SOI MOSFETs. Solid-State Electronics, 2013, 90, 116-120.	1.4	2
78	Performance Study of a Schottky Barrier Double-Gate MOSFET Using a Two-Dimensional Analytical Model. IEEE Transactions on Electron Devices, 2013, 60, 884-886.	3.0	5
79	A charge-based capacitance model for AlGaAs/GaAs HEMTs. Solid-State Electronics, 2013, 82, 38-40.	1.4	4
80	Automatic parameter extraction technique for gate leakage current modeling in double gate MOSFET. Solid-State Electronics, 2013, 89, 111-115.	1.4	0
81	Compact modeling solutions for short-channel SOI Schottky barrier MOSFETs. Solid-State Electronics, 2013, 82, 86-98.	1.4	10
82	Temperature dependent compact modeling of gate tunneling leakage current in double gate MOSFETs. Solid-State Electronics, 2013, 81, 124-129.	1.4	7
83	Mobility behavior and models for fully depleted nanocrystalline ZnO thin film transistors. Solid-State Electronics, 2013, 90, 134-142.	1.4	71
84	In-depth analysis and modelling of self-heating effects in nanometric DGMOSFETs. Solid-State Electronics, 2013, 79, 179-184.	1.4	13
85	Frequency and Voltage Dependence of the Capacitance of MIS Structures Fabricated With Polymeric Materials. IEEE Transactions on Electron Devices, 2013, 60, 2057-2063.	3.0	29
86	Compact physical models for gate charge and gate capacitances of AlGaIn/GaN HEMTs. , 2013, , .		4
87	A compact charge-based physical model for AlGaIn/GaN HEMTs. , 2013, , .		0
88	Compact Charge-Based Physical Models for Current and Capacitances in AlGaIn/GaN HEMTs. IEEE Transactions on Electron Devices, 2013, 60, 3746-3752.	3.0	70
89	A compact charge-based physical model for AlGaIn/GaN HEMTs. , 2013, , .		0
90	COMPACT MODELING OF DOUBLE AND TRI-GATE MOSFETs. International Journal of High Speed Electronics and Systems, 2013, 22, 1350004.	0.7	0

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91	Complex 2D Electric Field Solution in Undoped Double-gate MOSFETs. IETE Journal of Research, 2012, 58, 197.	2.6	1
92	2D Analytical Calculation of the Parasitic Source/Drain Resistances in DG-MOSFETs Using the Conformal Mapping Technique. IETE Journal of Research, 2012, 58, 205.	2.6	6
93	Gate leakage current partitioning in nanoscale double gate MOSFETs, using compact analytical model. Solid-State Electronics, 2012, 75, 22-27.	1.4	5
94	Effect of interface charge on the dc bias stress-induced deformation and shift of the transfer characteristic of amorphous oxide thin-film transistors. Microelectronics Reliability, 2012, 52, 1342-1345.	1.7	11
95	Analytical modeling of surface-potential and drain current in AlGaAs/GaAs HEMT devices. , 2012, , .		4
96	Analytical modeling of bare surface barrier height and charge density in AlGaIn/GaN heterostructures. Applied Physics Letters, 2012, 101, .	3.3	36
97	Effect of Density of States on Mobility in Small-Molecule n-Type Organic Thin-Film Transistors Based on a Perylene Diimide. IEEE Electron Device Letters, 2012, 33, 1201-1203.	3.9	23
98	Modeling the behavior of amorphous oxide thin film transistors before and after bias stress. Microelectronics Reliability, 2012, 52, 2532-2536.	1.7	20
99	Optimised design of an organic thin-film transistor amplifier using the gm/ID methodology. IET Circuits, Devices and Systems, 2012, 6, 136.	1.4	5
100	Analytical compact modeling framework for the 2D electrostatics in lightly doped double-gate MOSFETs. Solid-State Electronics, 2012, 69, 72-84.	1.4	25
101	An analytical compact model for Schottky-barrier double gate MOSFETs. Solid-State Electronics, 2011, 64, 78-84.	1.4	27
102	Charge-Based Modeling of Junctionless Double-Gate Field-Effect Transistors. IEEE Transactions on Electron Devices, 2011, 58, 2628-2637.	3.0	218
103	A physical compact DC drain current model for long-channel undoped ultra-thin body (UTB) SOI and asymmetric double-gate (DG) MOSFETs with independent gate operation. Solid-State Electronics, 2011, 57, 61-66.	1.4	15
104	2D analytical calculation of the electric field in lightly doped Schottky barrier double-gate MOSFETs and estimation of the tunneling/thermionic current. Solid-State Electronics, 2011, 63, 119-129.	1.4	13
105	New numerical low frequency noise model for front and buried oxide trap density characterization in FDSOI MOSFETs. Microelectronic Engineering, 2011, 88, 1286-1290.	2.4	8
106	Influence of P3HT:PCBM blend preparation on the active layer morphology and cell degradation. Microelectronics Reliability, 2011, 51, 597-601.	1.7	23
107	Impact of the fringing capacitance at the back of thin-film transistors. Organic Electronics, 2011, 12, 936-949.	2.6	12
108	Compact model for long-channel cylindrical surrounding-gate MOSFETs valid from low to high doping concentrations. Solid-State Electronics, 2011, 55, 13-18.	1.4	21

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109	ELECTRICAL PROPERTIES OF P3HT (POLY [3-HEXYLTHIOPHENE])/n-TYPE CRYSTALLINE SILICON (n-c-Si) SOLAR CELLS. International Journal of High Speed Electronics and Systems, 2011, 20, 749-773.	0.7	1
110	Study of potential high- $k$ dielectric for UTB SOI MOSFETs using analytical modeling of the gate tunneling leakage. Semiconductor Science and Technology, 2011, 26, 115002.	2.0	16
111	EFFECT OF PROCESS VARIATIONS ON AN OTFT COMPACT MODEL PARAMETERS. International Journal of High Speed Electronics and Systems, 2011, 20, 815-828.	0.7	4
112	CHARGE BEHAVIOR IN ORGANIC THIN FILM TRANSISTORS. International Journal of High Speed Electronics and Systems, 2011, 20, 727-748.	0.7	1
113	Implementation of the symmetric doped double-gate MOSFET model in Verilog-A for circuit simulation. International Journal of Numerical Modelling: Electronic Networks, Devices and Fields, 2010, 23, 88-106.	1.9	15
114	2D analytical calculation of the electrostatic potential in lightly doped Schottky barrier Double-Gate MOSFET. Solid-State Electronics, 2010, 54, 1372-1380.	1.4	19
115	The Equivalent-Thickness Concept for Doped Symmetric DG MOSFETs. IEEE Transactions on Electron Devices, 2010, 57, 2917-2924.	3.0	24
116	Modeling the behavior of charge carrier mobility with temperature in thin-film polymeric transistors. Microelectronic Engineering, 2010, 87, 2565-2570.	2.4	22
117	Effect of active layer thickness on the electrical characteristics of polymer thin film transistors. Organic Electronics, 2010, 11, 1920-1927.	2.6	38
118	Compact capacitance modeling of a 3-terminal FET at zero drain-source voltage. Solid-State Electronics, 2010, 54, 520-523.	1.4	5
119	Analytical modeling of the gate tunneling leakage for the determination of adequate high- $k$ dielectrics in double-gate SOI MOSFETs at the 22nm node. Solid-State Electronics, 2010, 54, 1083-1087.	1.4	20
120	Stability of PMMA on P3HT PTFTs under stress. Solid-State Electronics, 2009, 53, 1063-1066.	1.4	10
121	Direct protein detection with a nano-interdigitated array gate MOSFET. Biosensors and Bioelectronics, 2009, 24, 3531-3537.	10.1	40
122	MIS polymeric structures and OTFTs using PMMA on P3HT layers. Solid-State Electronics, 2008, 52, 53-59.	1.4	50
123	Universal compact model for long- and short-channel Thin-Film Transistors. Solid-State Electronics, 2008, 52, 400-405.	1.4	61
124	Modeling of potentials and threshold voltage for symmetric doped double-gate MOSFETs. Solid-State Electronics, 2008, 52, 830-837.	1.4	62
125	Mobility model for compact device modeling of OTFTs made with different materials. Solid-State Electronics, 2008, 52, 787-794.	1.4	89
126	Compact model for short channel symmetric doped double-gate MOSFETs. Solid-State Electronics, 2008, 52, 1064-1070.	1.4	140

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127	Compact model of output conductance in nanoscale bulk MOSFET based on 2D analytical calculations. Solid-State Electronics, 2008, 52, 1722-1729.	1.4	0
128	Compact charge and capacitance modeling of undoped ultra-thin body (UTB) SOI MOSFETs. Solid-State Electronics, 2008, 52, 1867-1871.	1.4	19
129	Conduction mechanisms of silicon oxide/titanium oxide MOS stack structures. Microelectronics Reliability, 2008, 48, 370-381.	1.7	22
130	Precise Modeling Framework for Short-Channel Double-Gate and Gate-All-Around MOSFETs. IEEE Transactions on Electron Devices, 2008, 55, 2678-2686.	3.0	45
131	A Quasi-Two-Dimensional Compact Drain-Current Model for Undoped Symmetric Double-Gate MOSFETs Including Short-Channel Effects. IEEE Transactions on Electron Devices, 2008, 55, 1441-1448.	3.0	56
132	Reversible Electrical Characteristics in PMMA on P3HT OTFTs. ECS Transactions, 2007, 9, 383-388.	0.5	5
133	Improved Compact Model for Symmetric Doped Double-Gate MOSFETs. ECS Transactions, 2007, 9, 47-56.	0.5	1
134	A CAD model of Nanoscale Double-Gate MOSFET for RF and Noise applications including quantum and non-stationary effects. , 2007, , .		0
135	Modeling Of Thin Film Transistors with Non-Ideal Contacts. ECS Transactions, 2007, 8, 165-170.	0.5	2
136	A Compact Quantum Model of Nanoscale Double-Gate MOSFET for RF and Noise Simulations. , 2007, , .		1
137	Analytical predictive modeling for the study of the scalability limits of multiple gate MOSFETs. Solid-State Electronics, 2007, 51, 414-422.	1.4	15
138	Optimized parameter extraction using fuzzy logic. Solid-State Electronics, 2007, 51, 683-690.	1.4	10
139	Compact model for highly-doped double-gate SOI MOSFETs targeting baseband analog applications. Solid-State Electronics, 2007, 51, 655-661.	1.4	54
140	Analytical Model of the Threshold Voltage and Subthreshold Swing of Undoped Cylindrical Gate-All-Around-Based MOSFETs. IEEE Transactions on Electron Devices, 2007, 54, 572-579.	3.0	133
141	Two-Dimensional Analytical Threshold Voltage and Subthreshold Swing Models of Undoped Symmetric Double-Gate MOSFETs. IEEE Transactions on Electron Devices, 2007, 54, 1402-1408.	3.0	99
142	A 3-D Analytical Physically Based Model for the Subthreshold Swing in Undoped Trigate FinFETs. IEEE Transactions on Electron Devices, 2007, 54, 2487-2496.	3.0	56
143	Compact RF Modeling of Multiple-Gate MOSFETs. , 2006, , .		3
144	Amorphous silicon carbide TFTs. Solid-State Electronics, 2006, 50, 460-467.	1.4	5

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145	Two-dimensional analytical threshold voltage roll-off and subthreshold swing models for undoped cylindrical gate all around MOSFET. Solid-State Electronics, 2006, 50, 805-812.	1.4	27
146	C $\alpha$ -continuous high-temperature model for low-doped accumulation mode silicon-on-insulator pMOSFETs. Solid-State Electronics, 2006, 50, 1261-1268.	1.4	0
147	Electrical studies of semiconductor-dielectric interfaces. Journal of Materials Science: Materials in Electronics, 2006, 17, 663-683.	2.2	7
148	RF and noise performance of double gate and single gate SOI. Solid-State Electronics, 2006, 50, 826-842.	1.4	46
149	Compact-Modeling Solutions For Nanoscale Double-Gate and Gate-All-Around MOSFETs. IEEE Transactions on Electron Devices, 2006, 53, 2128-2142.	3.0	91
150	Comment on "New Current-Voltage Model for Surrounding-Gate Metal Oxide Semiconductor Field-Effect Transistors". Japanese Journal of Applied Physics, 2006, 45, 6057-6057.	1.5	1
151	RF and Noise Performance of Multiple-Gate SOI MOSFETs. , 2006, , .		4
152	Effect of localized traps on the anomalous behavior of the transconductance in nanocrystalline TFTs. Microelectronics Reliability, 2005, 45, 1161-1166.	1.7	2
153	Accurate modeling and parameter extraction method for organic TFTs. Solid-State Electronics, 2005, 49, 1009-1016.	1.4	140
154	A numerical study of scaling issues for trench power MOSFETs. Solid-State Electronics, 2005, 49, 965-975.	1.4	7
155	A charge-based continuous model for submicron graded-channel nMOSFET for analog circuit simulation. Solid-State Electronics, 2005, 49, 1683-1692.	1.4	10
156	Explicit Continuous Model for Long-Channel Undoped Surrounding Gate MOSFETs. IEEE Transactions on Electron Devices, 2005, 52, 1868-1873.	3.0	198
157	A simple model of the nanoscale double gate MOSFET based on the flux method. Physica Status Solidi C: Current Topics in Solid State Physics, 2005, 2, 3086-3089.	0.8	4
158	Analog performance of the nanoscale double-gate metal-oxide-semiconductor field-effect-transistor near the ultimate scaling limits. Journal of Applied Physics, 2004, 96, 5271-5276.	2.5	35
159	Modeling of Nanoscale Gate-All-Around MOSFETs. IEEE Electron Device Letters, 2004, 25, 314-316.	3.9	136
160	Improved Direct Determination of MOSFET Saturation Voltage Using Fourier Techniques. IEEE Transactions on Electron Devices, 2004, 51, 2073-2077.	3.0	4
161	Modeling and parameter extraction procedure for nanocrystalline TFTs. Solid-State Electronics, 2004, 48, 103-109.	1.4	24
162	Noise modeling in fully depleted SOI MOSFETs. Solid-State Electronics, 2004, 48, 813-825.	1.4	33

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163	Continuous Analytic $I_{DS}$ Model for Surrounding-Gate MOSFETs. IEEE Electron Device Letters, 2004, 25, 571-573.	3.9	254
164	SOI n-MOSFET low-frequency noise measurements and modeling from room temperature up to 250°C. IEEE Transactions on Electron Devices, 2002, 49, 1289-1295.	3.0	28
165	DC SPICE model for nanocrystalline and microcrystalline silicon TFTs. IEEE Transactions on Electron Devices, 2002, 49, 1979-1984.	3.0	14
166	Deep-submicron drain current to radio frequency silicon on insulator metal oxide semiconductor field-effect transistor macromodel for designing microwave circuits. International Journal of RF and Microwave Computer-Aided Engineering, 2002, 12, 428-438.	1.2	0
167	Extraction method for polycrystalline TFT above and below threshold model parameters. Solid-State Electronics, 2002, 46, 2295-2300.	1.4	29
168	Fully depleted SOI CMOS technology for heterogeneous micropower, high-temperature or RF microsystems. Solid-State Electronics, 2001, 45, 541-549.	1.4	81
169	Self-heating and kink effects in a-Si:H thin film transistors. IEEE Transactions on Electron Devices, 2000, 47, 387-397.	3.0	54
170	A short-channel DC SPICE model for polysilicon thin-film transistors including temperature effects. IEEE Transactions on Electron Devices, 1999, 46, 1146-1158.	3.0	117
171	Modeling and simulation of single- and multiple-gate 2D MESFETs. IEEE Transactions on Electron Devices, 1999, 46, 1742-1748.	3.0	8
172	A physically-based $C_{int}$ -continuous model for accumulation-mode SOI pMOSFETs. IEEE Transactions on Electron Devices, 1999, 46, 2295-2303.	3.0	16
173	Microwave Simulation on the Performance of High Power GaN/AlGaIn Heterostructure Field Effect Transistors. Physica Status Solidi A, 1999, 176, 205-208.	1.7	2
174	An Improved $C_{int}$ -Continuous Small-Geometry MOSFET Modeling for Analog Applications. Analog Integrated Circuits and Signal Processing, 1997, 13, 241-259.	1.4	20
175	Unified substrate current model for MOSFETs. Solid-State Electronics, 1997, 41, 87-94.	1.4	22
176	A physically-based $C_{int}$ -continuous fully-depleted SOI MOSFET model for analog applications. IEEE Transactions on Electron Devices, 1996, 43, 568-575.	3.0	53
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